STRUCTURE AND KINETICS
OF DEFECTS IN SILICON

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NATIONAL AERONAUTICS AND SPACE ADMINISTRATION

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ABSTRACT

This paper reviews defects in the diamond-type lattice with special emphasis on silicon which is used as the basic material in the fabrication of solar cells in space programs. The defects are classified as first, second, and higher generation defects, according to their complexity. Some of these defects include vacancies and interstitials (as in lithium, for example) which are first generation defects capable of migrating above certain temperatures and trapping charge carriers. These first generation defects, because of their mobility, can form more complicated defects, such as the Si-A and Si-E centers. The properties of such defects have been systematically tabulated. A short discussion is given on some simple models of the kinetics of such defects. A comprehensive bibliography is given at the end of the review which should help the uninitiated commencing research in this field.
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REVIEW OF DEFECTS IN THE DIAMOND-TYPE LATTICE

Review of the Diamond Lattice

The space lattice of diamond consists of two interpenetrating face-centered sublattices centered at (0, 0, 0) and (1/4, 1/4, 1/4), respectively, as shown in Figure 1. Since the diamond structure is very inefficient in packing atoms as compared with the face-centered and body-centered lattices, it is a relatively empty structure. Each atom in the diamond structure is at the center of a tetrahedron with the nearest neighbor atoms at the vertices. Because of this, the inter-atomic forces are not only central but angular-dependent. This complicates matters when calculating the lattice vibrational spectrum (Reference 2). A modified OPW method employing a pseudopotential has been successful in calculating the band structure of elements crystallizing in the diamond structure (References 3 through 6). Carbon, silicon, and germanium are some of these elements, the latter two being elemental semiconductors. Currently, silicon is being extensively used as solar cell material in the space program. Therefore, most attention will be focused on it.

First-Generation Defects in the Diamond Lattice

First-generation defects are defined here as simple defects which are composed of not more than one defect.
The Lattice Vacancy

One of the simplest types of defect is the lattice vacancy—an atom missing from its lattice site shown as A in Figure 2. The electronic rebonding after the defect has relaxed is shown in Figure 3. There are three equivalent bond positions for the model; (26, 34), (23, 64) and (24, 63). A study in the temperature range of 14° to 20° K indicates an activation energy for reorientation of bonds from one equivalent configuration to another of only 0.01 to 0.02 eV at 20° K. This reorientation can also be accomplished by applying a uniaxial compressional stress along a cubic axis (Reference 7). The vacancy in silicon is capable of trapping electrons and existing in several charge states. In p-type Si, it is usually neutral, and in n-type Si a single or double negative state may exist depending upon the position of the Fermi level (see Figure 4). A positive-charge state exists but can only be seen if the sample is illuminated, since the trapping level of the positive vacancy usually lies below the acceptor impurity level. The vacancy is also capable of migrating throughout the lattice at room temperatures and below (see Figure 5). This is not surprising.
THE CIRCLED CHARGE STATES ARE THOSE OBSERVED BY EPR.

Figure 4—Electrical levels associated with some of the defects (after G. D. Watkins, Reference 8).

Figure 5—Schematic scheme for the migration of a vacancy in the diamond lattice (after R. A. Swalin, Reference 9).
since, as has been noted, the lattice is relatively open. Currently, it appears that the migration energy of the vacancy is dependent on its charge state, being 0.33 eV for a neutral vacancy and less than 0.20 eV for either negative-charge state. At this point it still is not known if the 0.20 eV energy is associated with a single or double negative state (Reference 10).

The Interstitial

Another simple type of defect is the interstitial shown as B and C in Figure 2. B represents the host atom in a nonlattice position. In the case of silicon, this would be the silicon atom. Thus far, the interstitial silicon atom has escaped detection (Reference 7). All experimental evidence indicates that the interstitial silicon is very mobile—much more than the vacancy. C represents an impurity interstitial which also can migrate throughout the lattice. Perhaps the most investigated impurity interstitials have been gold, silver, and lithium, of which lithium is of most interest. The interstitial can occupy two different symmetry sites in the lattice, the interstitial position halfway between two next neighboring atoms along a (001) lattice axis, called the tetrahedral configuration, and the position halfway between two next neighboring tetrahedral interstitial positions called the hexagonal configuration (see Figure 6). Most interstitials carry an electric charge when they enter the lattice. Lithium, copper, silver, and gold do so in silicon (References 12 through 16). However, the last three impurities can also exist as substitutional defects, and their diffusion is by the "dissociative mechanism" (Reference 17). These elements can dissolve in Si or Ge in two states, interstitially and substitutionally. To diffuse substitutionally, the host crystal must have a supply of vacancies available. Therefore, this facet of diffusion will depend strongly on the dislocation density in the crystal. The experimental values for the migration energy of Li in Si and Ge are 0.66 and 0.51 eV, respectively (Reference 18).

It is also known in radiation damage studies that interstitial Si atoms can replace dopant atoms, the dopant atoms becoming interstitials. For instance, an EPR spectrum arising from Al has been observed in aluminum-doped Si (p-type) irradiated at 4° K. There is evidence that other
group III impurities behave similarly (Reference 8). The trapping levels of the interstitial Al atom are shown in Figure 4.

The Si-O-Si Configuration

This defect, which is usually seen in crystals grown in quartz crucibles, is shown as D in Figure 2. The defect will hereinafter be called the "interstitial" oxygen atom. This basic defect was first observed by its 9μ-band excitation about ν3 shown in Figure 7. An 11.7μ-band is associated with the corresponding defect in Ge (Reference 19). There are six equivalent positions; however, Hrostowski and Alder point out that the barrier for reorientation from one equivalent position to another is so small that at room temperature the Si-O-Si molecule is essentially a free rotator (Reference 20). If a uniaxial stress is applied at an elevated temperature, the <111> direction will become nonequivalent and the oxygen atom will jump to a completely new orientation. The energy required to do this is 2.561 ± 0.005 eV. This is equivalent to the energy needed for the diffusion of oxygen in the silicon lattice (References 21 and 22). The energy required for migration of the defect is so large that treating the oxygen atom as a stable defect at room temperature and below is a good approximation. This defect plays an important role in second-generation defects, discussed below.

Substitutional Defects

Substitutional defects are shown as E and F in Figure 2. These defects consist of foreign atoms occupying a lattice site of the host crystal. These impurities may enter as neutral or charged substitutional defects, E being a group V donor and F being a group III acceptor. Although, when in a substitutional position, these atoms look like Si, nevertheless they are defects and should be treated as such. This will be more evident in the following section.

Second-Generation Defects

Early in the history of defects in Si and Ge, all trapping levels were thought to be due to isolated vacancies and interstitials, first-generation defects. This model soon proved to be incomplete. In reality, the vacancy not only can be a trapping and recombination center, but can migrate throughout the lattice and interact with other defects to form second-generation defects.

The Divacancy

In this defect configuration, bonding occurs between a-d and a-d' with the unpaired electron (in the solid line) between b-b', as shown in Figure 8. Besides this, there are two other equivalent
configurations: bonding a-b and a'-b' with the unpaired electron on d-d', and bonding b-d and b'-d' with the unpaired electron on a-a' (see Figure 9). By stressing the crystal uniaxially, the majority of defects can be preferentially aligned in one direction. These preferentially aligned defects can then be frozen in at a low temperature. Then by a slow isochronal anneal, the energy of reorientation of the electronic bond can be measured. In the temperature range from 40° to 110° K, line broadening is observed in the EPR spectrum of the defect (Reference 24). The energy of activation for electronic reordering is 0.06 eV. Nevertheless, another degree of freedom of the divacancy is about a line joining the vacancies. In order to change the orientation of this axis, an energy of 1.3 eV is required (Reference 24). This is actually the energy needed for the migration of such a defect. These various energies are classified in Figure 10. The trapping levels associated with the divacancy are rather complicated, as can be seen from Figure 4. The energy needed for the complete breakup of the divacancy is approximately 1.85 eV; i.e., the sum of the energy needed to separate the divacancy to the first nearest neighbor, 1.3 eV, and the corresponding energy needed to move the vacancies away from each other more than one nearest-neighbor distance, 0.65 eV (Reference 24). During low-energy electron irradiation, most of the divacancies are correlated; this is demonstrated by the anisotropy, R, of the vacancy orientation versus bombarding electron energy, where R is the ratio of the number of divacancies orientated along the beam axis to that along another, <111>, direction. For bombardment energies less than 1.0 MeV, R = 2.0 (Reference 25). At these bombardment energies, the rate of growth of divacancies is less governed by the diffusion of vacancies than at higher energies. The 1.8\,\mu, 3.3\,\mu and 3.9\,\mu absorption bands have since been associated with electronic energy transitions of the divacancy (Reference 26). These bands are
associated with excitation charge carriers into traps. As a result there is no photoconductivity connected with these absorption bands.

The Oxygen-Vacancy Defect in Si or the Si-A Center

In migrating throughout the lattice, the vacancy may encounter the structure in Figure 7. If so, it becomes trapped by the "interstitial" oxygen atom and forms the oxygen-vacancy complex shown in Figure 11. The configuration has an acceptor level at $E_c - 0.17$ eV. The oxygen-vacancy defect can capture an electron. After this, a hole can be captured and recombined with the electron. The defect is neutral when capturing an electron, and negatively charged before it captures a hole. The capture cross section is for electrons, $\sigma_e \approx 10^{-16}$ cm$^2$, and for holes, $\sigma_h \approx 10^{-14}$ cm$^2$ (Reference 27). Again, there are six equivalent configurations for the oxygen-vacancy defect, the energy required for electronic reorientation being $0.20 \pm 0.03$ eV (Reference 28). Also, the defect itself can change positions corresponding to an applied stress. The energy required corresponds to $0.38 \pm 0.04$ eV for a neutral oxygen-vacancy defect (Reference 28). This energy is the thermal-activated switching of the oxygen atom from one pair of silicon atoms to another. The oxygen-vacancy defect gives rise to an impurity vibrational band at $12\mu$ (Reference 29). The trapping level at $E_c - 0.17$ eV and the $12\mu$ band disappear upon an isochronal anneal to $500^\circ$C, indicating an activation energy of 1.3 eV for possible breakup (Reference 30).

The Phosphorus-Vacancy Defect in Si or the Si-E Center

As in the oxygen-vacancy defect, the vacancy, if encountering a phosphorus atom in a substitutional position, can become trapped and thus form the phosphorus-vacancy defect shown in Figure 12. Again there are three equivalent electronic orientations. The energy needed to activate the hopping of an unpaired electron from one configuration to another is 0.06 eV (Reference 31).
The energy required to change the direction of the phosphorus-vacancy axis by rearranging atoms through a compression along a 110 axis at high temperature is 0.93 ± 0.05 eV (Reference 31). This reorientation amounts to diffusion of the phosphorus-vacancy pair through the lattice. It is not known if the phosphorus-vacancy defect breaks up or diffuses as an entity to traps, as pointed out by Watkins. Some annealing experiments give 0.93 eV as the activation energy for annealing, suggesting diffusion to traps (Reference 27). An argument by Watkins and Corbett gives the energy of annealing as 1.18 eV. This information is condensed in Figure 13. This defect has a deep acceptor level at $E_c - 0.40$ eV. So far, there is no evidence of an associated lattice vibrational band. The defect has a hole capture cross section of $1.1 \times 10^{-13}$ cm$^2$ (References 27 and 32).

Figure 12—A model of the phosphorus-vacancy complex or the Si-E center.

Figure 13—The potential energy (in eV) of a vacancy in the vicinity of a substitutional phosphorus atom (after J. W. Corbett, G. D. Watkins, R. L. Chrenko, and R. S. McDonald, Reference 29).

**Other Impurity-Vacancy Defects**

The silicon crystal can also be doped with other group V elements besides phosphorus. Studies on silicon doped with As, Sb, and Bi indicate that each of these impurities can form an impurity-vacancy defect in Si with trapping levels around $E_c - 0.40$ eV and configurations similar to the phosphorus-vacancy complex. An empirical formula has been obtained for the activation energy of annealing these centers:

$$E_a = 3.6r - 3.0 \text{ eV},$$

where $E_a$ is the activation energy for annealing the defect, $r$ is the tetrahedral covalent radius of the impurity atom of group V in Å (Reference 33).

The $A_s$-vacancy defect has a hole capture cross section of $4 \times 10^{-14}$ cm$^2$ (Reference 27).

There is also a possibility of group III atoms contributing to impurity-vacancy defects. For instance, in Al-doped vacuum floating-zone Si, an EPR spectrum is observed to grow; this is
associated with the disappearance of the free vacancy spectrum along with the A1 (Reference 27) hyperfine interaction (Reference 8). No trapping levels have so far been associated with this A1-vacancy defect.

*Ion-Pairing*

Perhaps the most extensively studied interstitial in the Si lattice is the Li⁺ ion which enters the lattice as a donor (References 12 and 34). In p-type Si, the Li⁺ interstitials are known to interact with the p-type dopant atoms to form relatively immobile Li-dopant ion pairs (References 35, 36, and 37). It is also known that the Li⁺ interstitial will interact with the "interstitial" oxygen atom to form (Li-O)⁺ defects. The dissociation or annealing energy of such complexes is obtained from the ratio of the effective drift mobility of Li in samples with oxygen concentrations up to $1.3 \times 10^{18} \text{ cm}^{-3}$ to known drift mobility of free Li, and is 0.42 eV (Reference 37). The absorption peaks for Li-B pairing have been observed by W. G. Spitzer and M. Waldner and are reproduced in Table 1 (Reference 38). Some of their conclusions are:

1. The modes at 564 or 584 and at 655 or 681 cm⁻¹ do not involve much Li motion.
2. The position of these modes does depend upon a change of the local environment around the boron atom due to the Li ion, paired with the boron.
3. The force constant between the paired Li and B is not great enough to cause a characteristic Li-B vibration.

<table>
<thead>
<tr>
<th>Isotopic pair/cm⁻¹</th>
<th>$^{11}B$ &amp; $^{7}Li$</th>
<th>$^{10}B$ &amp; $^{7}Li$</th>
<th>$^{11}B$ &amp; $^{6}Li$</th>
<th>$^{10}B$ &amp; $^{6}Li$</th>
</tr>
</thead>
<tbody>
<tr>
<td>Low-frequency peak</td>
<td>522 \ 522</td>
<td>534</td>
<td>534</td>
<td></td>
</tr>
<tr>
<td>Central-frequency peak</td>
<td>564 \ 584</td>
<td>564 \ 584</td>
<td></td>
<td></td>
</tr>
<tr>
<td>High-frequency peak</td>
<td>655 \ 681</td>
<td>657 \ 683</td>
<td></td>
<td></td>
</tr>
<tr>
<td>Peak due to unpaired boron</td>
<td>620 \ 644</td>
<td></td>
<td></td>
<td></td>
</tr>
</tbody>
</table>

**Higher-Generation Defects**

It was mentioned that the phosphorus-vacancy defect could migrate at an energy and become trapped, possibly forming another defect. Also, the migration energy of the oxygen-vacancy complex is such that this entity could migrate and form higher-order defects. Obviously the classification of these defects along with other more complicated defects can get out of hand. Therefore, the classification of defect conglomerations composed of three or more first-generation defects will be called higher-generation defects.
CWM Model for Annealing the Oxygen-Vacancy Defect

Upon monitoring the decay of the impurity vibrational band of the oxygen-vacancy defect in Si at 829 cm\(^{-1}\) (12\(\mu\)), Corbett, Watkins, and McDonald noticed the appearance of other new bands at 887 cm\(^{-1}\) (11.215\(\mu\)), 904 cm\(^{-1}\) (11.004\(\mu\)), 968 cm\(^{-1}\) (10.276\(\mu\)), and 1000 cm\(^{-1}\) (9.948\(\mu\)). The rise of the 887 cm\(^{-1}\) line is interpreted as the diffusion of an oxygen-vacancy defect to an "interstitial" oxygen site as shown in (a) of Figure 14, and is hereinafter called the CWM I defect. The remaining three bands would be caused by the addition of another "interstitial" oxygen atom to CWM I. This configuration shown as (b) in Figure 14 will be called the CWM 2 defect (Reference 39). As stated in Reference 39, these models are highly speculative. It is not known if either CWM 1 or 2 acts as trapping or recombination centers. Since the experiment of CWM, other spectra shown in Table 2 have been seen upon annealing the oxygen-vacancy defect. Four of the lines have been seen and correlated by two or more investigators, including the 12\(\mu\), 11.3\(\mu\), 11.0\(\mu\), and 9.0\(\mu\) lines (References 40, 41 and 42). (The slight differences between the values of Corbett, et al. and those of the other three investigators are due to a different measuring temperature.) This clearly demonstrates that the oxygen-vacancy defect need not decompose into its first-generation defects, but may form higher-generation defects. This may also be the case with other second-generation defects upon annealing.

![Figure 14-Tentative models for (a) the 887 cm\(^{-1}\) ir band and (b) 904-, 968-, and 1000-cm\(^{-1}\) bands (after E. M. Pell, Reference 35).](image)

Table 2

<table>
<thead>
<tr>
<th>Investigator</th>
<th>Dominant Band in (Wave Numbers, Cm(^{-1})) in Microns</th>
</tr>
</thead>
<tbody>
<tr>
<td></td>
<td>Cm(^{-1})</td>
</tr>
<tr>
<td>------------------------------</td>
<td>------------</td>
</tr>
<tr>
<td>R. E. Whan</td>
<td>20.5</td>
</tr>
<tr>
<td>(Reference 40)</td>
<td></td>
</tr>
<tr>
<td>J. C. Corelli, et al.</td>
<td></td>
</tr>
<tr>
<td>(Reference 41)</td>
<td></td>
</tr>
<tr>
<td>J. W. Corbett, et al.</td>
<td></td>
</tr>
<tr>
<td>(Reference 39)</td>
<td></td>
</tr>
<tr>
<td>H. Y. Fan</td>
<td></td>
</tr>
<tr>
<td>(Reference 42)</td>
<td></td>
</tr>
</tbody>
</table>
The Silicon K Center

This defect is one of the predominant paramagnetic defects introduced into p-type silicon. This center requires oxygen and acts as a hole trap at $E_v + 0.30 \text{ eV}$. Its charge state can also change, depending on the position of the Fermi level (Reference 44). A speculative model proposed from EPR measurements by a group at RCA is shown in Figure 15 (Reference 45). Two oxygen-vacancy complexes can randomly migrate throughout the crystal and, upon a chance meeting, form such a defect configuration. The probability of this event occurring is more likely than two vacancies being trapped by a Si-O-O-Si molecule. Unfortunately, no impurity lattice vibrational mode has yet been seen or measured corresponding to this center. It would be interesting to see if any of the absorption peaks of the K-center correspond to any of those for CWM 1 or 2.

Conclusions

All the kinetic properties of the various defects are given in Table 3. The contributors to the various experimental values which are unreferenced in the table can be found in the main text, and

<table>
<thead>
<tr>
<th>Defect</th>
<th>Electronic Reorientation</th>
<th>Migration Energy</th>
<th>Annealing Energy</th>
<th>Associated Lattice Absorption Band ($\mu$)</th>
<th>Impurity Electronic Energy States</th>
</tr>
</thead>
<tbody>
<tr>
<td>Vacancy</td>
<td>0.01 - 0.02</td>
<td>0.30 (neutral)</td>
<td>-</td>
<td>-</td>
<td>three charged states</td>
</tr>
<tr>
<td>Silicon interstitial</td>
<td></td>
<td>0.20 (charged)</td>
<td>-</td>
<td>-</td>
<td></td>
</tr>
<tr>
<td>&quot;Interstitial&quot; oxygen</td>
<td>0.02</td>
<td>2.56</td>
<td>-</td>
<td>$9\mu$</td>
<td>none</td>
</tr>
<tr>
<td>Divacancy</td>
<td>0.06</td>
<td>1.3</td>
<td>1.89$^b$</td>
<td>-</td>
<td>double neg.</td>
</tr>
<tr>
<td>Oxygen-vacancy</td>
<td>0.20 0.03</td>
<td>0.38$^c$</td>
<td>1.3</td>
<td>$12\mu$</td>
<td>single neg. at $E_v - 0.17 \text{ eV}$</td>
</tr>
<tr>
<td>Phosphorus-vacancy</td>
<td>0.06$^d$</td>
<td>0.93 0.05</td>
<td>1.18$^e$</td>
<td>?</td>
<td>single neg. at $E_v - 0.40 \text{ eV}$</td>
</tr>
<tr>
<td>Li$^+$</td>
<td>-</td>
<td>0.655</td>
<td>-</td>
<td>-</td>
<td>acts as a donor</td>
</tr>
<tr>
<td>(Li - O)$^b$</td>
<td>-</td>
<td>-</td>
<td>0.42</td>
<td>?</td>
<td>acts as a donor</td>
</tr>
<tr>
<td>Li$^+$ + B$^-$</td>
<td>-</td>
<td>Continued:</td>
<td>-</td>
<td>see text</td>
<td></td>
</tr>
<tr>
<td>CWM 1</td>
<td>-</td>
<td>-</td>
<td>-</td>
<td>11.215 (887 cm$^{-1}$)</td>
<td></td>
</tr>
<tr>
<td>CWM 2</td>
<td>-</td>
<td>-</td>
<td>-</td>
<td>9.948 (1000 cm$^{-1}$)</td>
<td></td>
</tr>
<tr>
<td>K-center</td>
<td>-</td>
<td>-</td>
<td>-</td>
<td>11.004 (904 cm$^{-1}$)</td>
<td>$E_v + 0.3 \text{ eV}$, (hole trap)</td>
</tr>
</tbody>
</table>

(a) May be a single or double negative charge state.
(b) This is presumably for a neutral divacancy. This energy probably depends on the charge state of the defect.
(c) Energy required to break an Si-O bond for neutral Si-A defect
(d) The energy required for the hopping of one unpaired electron between the three equivalent directions.
(e) From EPR measurements.
(f) From electrical measurements.
need not be repeated in the table. This list of defects is by no means exhaustive. Future developments will add to the list and disagreements will persist, i.e.

1. Quenching experiments in p-type Si report an energy of migration of the interstitial of 0.31 eV (Reference 46).

2. No theoretical calculations substantiate any values for the experimental values of the energy of migration of either the vacancy or interstitial (References 47 and 40).

The vacancy is the defect which is responsible for most of the damage in the silicon lattice. Without it, most second- and higher-generation defects would not exist. Therefore, the importance of establishing a well based theoretical calculation which agrees with the experimental value of the migration energy of the vacancy cannot be overstated.

**KINETICS OF DEFECT PRODUCTION AND MIGRATION**

The simple laws of mass action can be used with some success in following the various interactions of defects in solids. In this simple notation, the creation of an impurity-vacancy defect by a source of radiation, $\phi$, can be schematically written in the form of three reactions:

$$\phi \xrightarrow{K_0} V + i,$$  

$$V + i \xrightarrow{K_1} \text{annihilation},$$  

$$V + I \xrightarrow{K_2} C,$$

where

- $V$ is the free-vacancy concentration,
- $i$ is the free-interstitial concentration,
- $I$ is the free-impurity concentration,
- $C$ is the 2nd-generation defect concentration.

These concentrations are measured in atomic fractions. The side conditions are:

$$i = V - C,$$

$$I = I_0 - C,$$

where $I_0$ is the impurity concentration at time $t = t_0$. The reaction rates, $K_i$, are defined as follows:

$$K_i = \gamma_i \nu_i \exp\left(-\frac{E_i}{kT}\right),$$
where

$\gamma_i$ is the coordination number,
$\nu_i$ is the frequency factor,
$E_i$ is the energy associated with the particular reaction,
$k$ is Boltzmann's constant,
$T$ is the temperature.

This model assumes, of course, that the interstitials are captured at sinks with rates much less than the $K_i$'s defined. Actually, the reaction rate for trapping of interstitials by sinks such as the surface is so small compared to the other reaction rates that it can be neglected. Reaction 1 is just the creation of first-order defects (Frenkel pairs) through some source term $\phi$, with an efficiency factor $K_0$. Reaction 2 is the annihilation of these first-generation defects by chance meeting. Finally, reaction 3 is the trapping of vacancies by impurities to form second-generation defects, in this case impurity-vacancy defects. The differential equations become:

$$\frac{dV}{dt} = -K_2 I_0 V + K_3 C - K_1 V^2 + (K_2 - K_1) VC + K_0 \phi$$

$$\frac{dC}{dt} = K_2 I_0 V - K_3 C - K_2 VC$$

These have been solved by computer program; asymptotic analytic solutions have been obtained for long times, low temperatures, and $K_3 \approx 0$.

Reaction 3 is shown as being reversible. However, in the discussion of higher-generation defects, it is shown that the production of such defects is not only possible but likely. In annealing studies where the source term is now zero, the kinetic scheme would have to be replaced by more complicated reactions. For example:

$$C \xrightarrow{K_5} V + I$$

$$C + C \xrightarrow{K_4} C_2$$

$$C + V \xrightarrow{K_5} C_3$$

and, if any interstitials are still present,

$$V + i \xrightarrow{K_i} \text{annihilation}$$

otherwise $K_i = 0$. The differential equations would then be

$$\frac{dC}{dt} = -K_3 C - K_4 C^2 - K_5 CV$$
In the case of the oxygen-vacancy defect in Si, reaction 7 would possibly be the production of the RCA K-center. At the present, higher-generation defects associated with the impurity oxygen atom have only been seen, but these reactions should not be ruled out for other impurities, such as the phosphorus-vacancy defect. In the case of measuring some electrical parameter, the "annealing" of the sample is usually seen as the trapping or expulsion of trapped carriers. If, upon "annealing", the resultant higher-generation defects were capable of trapping additional carriers, then there would be "reverse annealing". This can best be seen by counting charges:

\[
\frac{dC_2}{dt} = K_4 C^2, \quad (10)
\]

\[
\frac{dC_3}{dt} = K_5 CV, \quad (11)
\]

\[
\frac{dV}{dt} = K_3 C - K_1 V_i. \quad (12)
\]

The result of the anneal will be the additional loss of 1 charges. However, an isochronal measurement of the intensity of the defect absorption bands together with photoconductivity will only show forward annealing of C and production of C₂. An example of reverse annealing in the experiments of T. Nakano, et al. is shown in Figure 16. These curves are not atypical.

REFERENCES


"The aeronautical and space activities of the United States shall be conducted so as to contribute . . . to the expansion of human knowledge of phenomena in the atmosphere and space. The Administration shall provide for the widest practicable and appropriate dissemination of information concerning its activities and the results thereof."

—National Aeronautics and Space Act of 1958

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